



程轶

副教授

硕士生导师

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教育背景

大连理工大学 微电子学与固体电子学 博士

研究领域

研究方向为半导体发光材料与器件，主要从事宽带系半导体材料与器件的研究工作。

论文

- (1) Comprehensive study on Sb-doped zinc oxide films deposited on c-plane Al₂O₃ substrates, Journal of Materials Science: Materials in Electronics, 29, 11280–11285, 2018.
- (2) Influence of molar ratio of Sb/Zn on the crystal, electrical and optical properties of Sb-doped ZnO films, Journal of alloys and compounds, 699, 690-694, 2017.
- (3) Influence of substrate temperature on the optical properties of Sb-doped ZnO films prepared by MOCVD, Journal of Materials Science: Materials in Electronics, 28, 2602-2606, 2017.
- (4) Structural, morphological, FTIR and photoluminescence properties of gallium oxide thin films, Journal of Vacuum Science and Technology, 32(3), 03D119-1-4, 2014.
- (5) Research on the structural and optical stability of Ga₂O₃ films deposited by electron beam evaporation. Journal of Materials Science: Materials in Electronics, 24(12), 5122-5126, 2013.
- (6) Band gap broadening and photoluminescence properties investigation in Ga₂O₃ polycrystal. Journal of Materials Science: Materials in Electronics, 24(8), 2750-2754, 2013.
- (7) Influence of N₂ and O₂ anneal treatment on the optical band

代表性成果

gap of $\text{Ga}_2\text{O}_3:\text{Cu}$ polycrystalline films. Materials Science in Semiconductor Processing, 16(5), 1303-1307, 2013.

代表性项目

- (1) 中央高校基本科研业务费, 3132014086, 氧化镓发光材料结构特性与光致发光机理研究, 2014/01-2014/12, 已结题, 主持。
- (2) 中央高校基本科研业务费, 3132017057, 深紫外探测器的制备与物理性质研究, 2017/01-2017/12, 已结题, 主持。
- (3) 辽宁省博士科研启动基金, 201601079, 氧化镓薄膜的制备与性质的研究, 2016/01-2018/12, 在研, 主持。